

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

Claim 21. (currently amended): A semiconductor device comprising:
a gate insulating film and a gate electrode stacked in this order;
wherein said gate insulating film and said gate electrode are in contact with each other;

and

wherein said gate insulating film comprises a nitrogen containing high-dielectric-constant insulating film which has a structure in which nitrogen is introduced into metal oxide or metal silicate; and

the nitrogen concentration in said nitrogen containing high-dielectric-constant insulating film has a distribution in the direction of the film thickness; and

a position at which the nitrogen concentration in said nitrogen containing high-dielectric-constant insulating film reaches a maximum in the direction of the film thickness is present in a region at a distance from the silicon substrate.

Claim 22. (original): A semiconductor device according to Claim 21, wherein a position at which the nitrogen concentration in said nitrogen containing high-dielectric-constant insulating film reaches a maximum in the direction of the film thickness is present in a region at a distance of not less than 0.5 nm from the silicon substrate.